EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((FET or ((field adj effect) adj transistor)) same coordinates) and (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:52
L2	8	((FET or ((field adj effect) adj transistor)) same (coordinate\$2 or location\$2)) and (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:54
L3	0	((FET or ((field adj effect) adj transistor)) same (coordinate\$2 or location\$2)) same (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:54
L4	0	((FET or ((field adj effect) adj transistor)) same (coordinate\$2 or location\$2)) and (signal adj integrity) and (well adj edge)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:54
S1	2592	716/4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 11:24
S2	2000	716/5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 11:17
S3	2101	716/1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 11:17
S4	0	(716/4).ccls. and (identify\$4 or determin\$4) same (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 11:28
S5	1	(716/5).ccls. and (identify\$4 or determin\$4) same (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 11:28

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S6	0	(716/1).ccls. and (identify\$4 or determin\$4) same (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 11:29
S7	1	("716"/\$).ccls. and (identify\$4 or determin\$4) same (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF '	2006/04/28 11:29
58	2	(identify\$4 or determin\$4) same (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:20
S9	2	(identify\$4 or determin\$4) and (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:21
S10	1	((identify\$4 or determin\$4) and (FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)).CLM.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:21
S11	2	(FET or ((field adj effect) adj transistor)) and ((signal adj integrity) adj failure)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:22
S12	384	(FET or ((field adj effect) adj transistor)) and (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:22
S13	13	(FET or ((field adj effect) adj transistor)) same (signal adj integrity)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:24
S14	, 2	(FET or ((field adj effect) adj transistor)) same (signal adj integrity) same fail\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:23
S15	2	((FET or ((field adj effect) adj transistor)) same (signal adj integrity)) and ((threshold adj distance) same (well adj edge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:26

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S16	2	((FET or ((field adj effect) adj transistor)) same (signal adj integrity)) and ((threshold adj distance) and (well adj edge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:50
S17	2	((FET or ((field adj effect) adj transistor)) and (signal adj integrity)) and ((threshold adj distance) and (well adj edge))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:26
S18	. 1	(((FET or ((field adj effect) adj transistor)) and (signal adj integrity)) and ((threshold adj distance) and (well adj edge))). CLM.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/28 12:26



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